

P-Ch 30V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



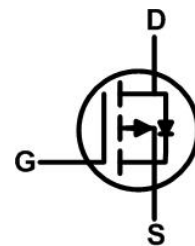
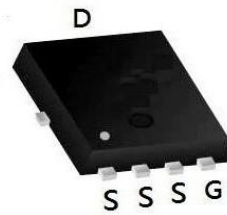
BVDSS	RDSON	ID
-30V	7.5mΩ	-55A

Description

The XR60P03D is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The XR60P03D meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN3333-8L Pin Configuration



Absolute Maximum Ratings (T_A = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _C =25°C	I _D	-55	A
	T _C =100°C		-30	
Pulsed Drain Current ¹		I _{DM}	-168	A
Single Pulse Avalanche Energy ²		EAS	45	mJ
Total Power Dissipation	T _C =25°C	P _D	37	W
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	R _{θJA}	75	°C/W
Thermal Resistance from Junction-to-Case	R _{θJC}	3.36	°C/W

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Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V
Gate-body Leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	V _{DS} = -30V, V _{GS} = 0V	-	-	-1	μA
	T _J =100°C		-	-	-100	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-	-2.5	V
Drain-Source On-Resistance ⁴	R _{DS(on)}	V _{GS} = -10V, I _D = -30A	-	7.5	10	mΩ
		V _{GS} = -4.5V, I _D = -15A	-	10	13	
Forward Transconductance ⁴	g _{fs}	V _{DS} = -5V, I _D = -30A	-	57	-	S
Dynamic Characteristics⁵						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz	-	2396	-	pF
Output Capacitance	C _{oss}		-	325	-	
Reverse Transfer Capacitance	C _{rss}		-	283	-	
Gate Resistance	R _g	f = 1MHz	-	10.5	-	Ω
Switching Characteristics⁵						
Total Gate Charge	Q _g	V _{GS} = -10V, V _{DS} = -15V, I _D = -30A	-	30	-	nC
Gate-Source Charge	Q _{gs}		-	5	-	
Gate-Drain Charge	Q _{gd}		-	7.5	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = -10V, V _{DD} = -15V, R _G = 3Ω, I _D = -30A	-	14.1	-	ns
Rise Time	t _r		-	20	-	
Turn-Off Delay Time	t _{d(off)}		-	94	-	
Fall Time	t _f		-	65	-	
Body Diode Reverse Recovery Time	t _{rr}	I _F = -30A, dI/dt = 100A/μs	-	19	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	9	-	nC
Drain-Source Body Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	I _S = -1A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	T _C =25°C	I _S	-	-	-55	A

Note :

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}= -25V, V_{GS}= -10V, L= 0.1mH, I_{AS}= -30A.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

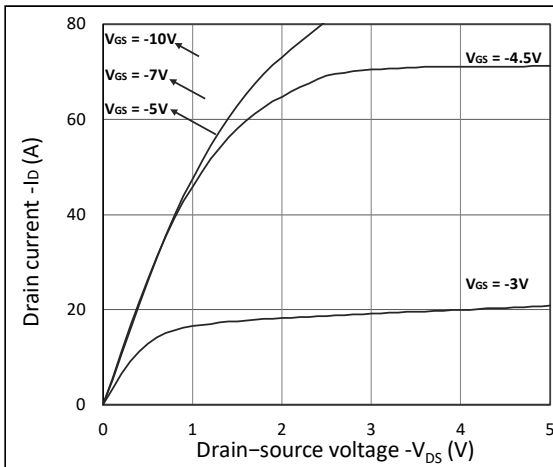


Figure 1. Output Characteristics

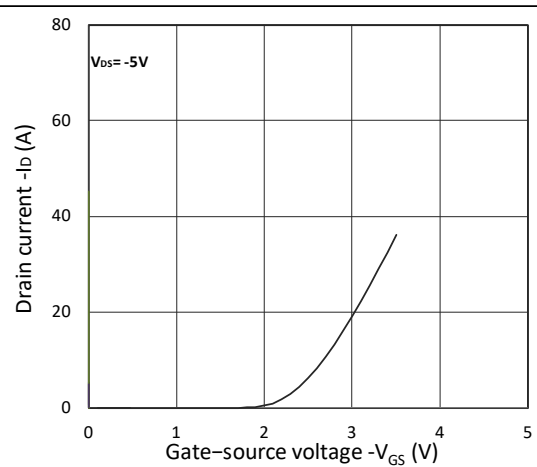


Figure 2. Transfer Characteristics

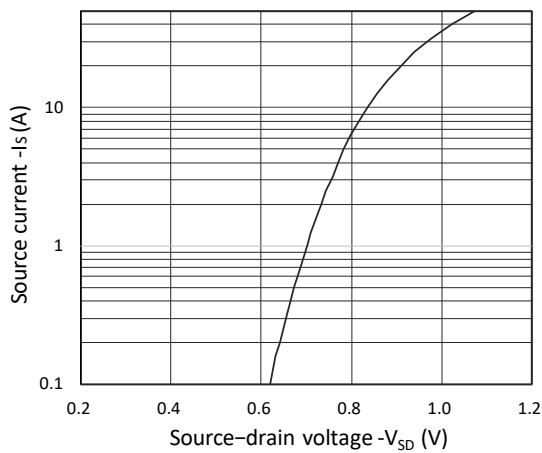


Figure 3. Forward Characteristics of Reverse

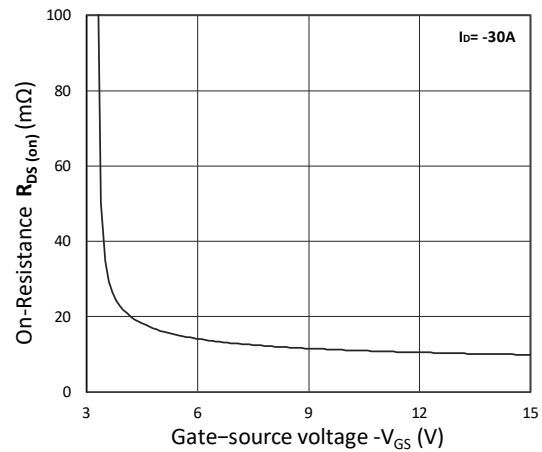


Figure 4. $R_{DS(on)}$ vs. V_{GS}

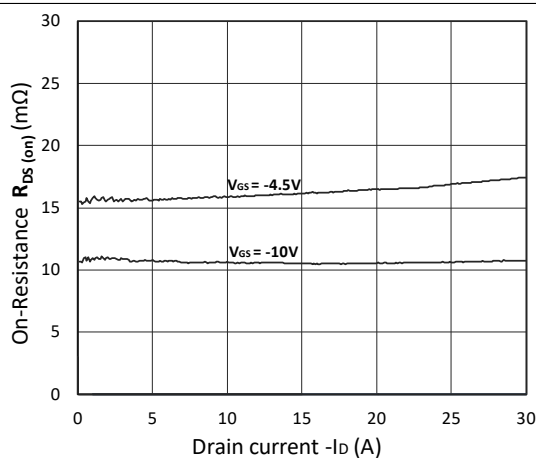


Figure 5. $R_{DS(on)}$ vs. I_D

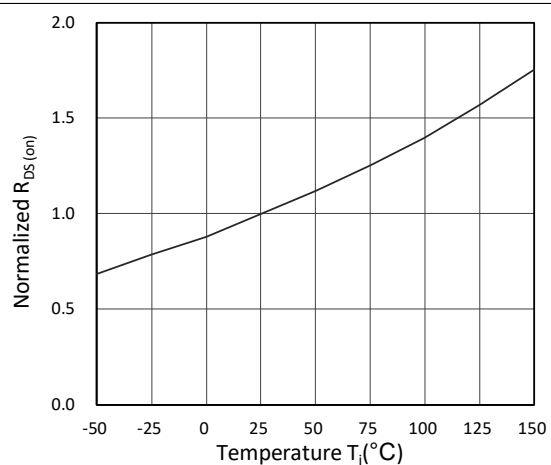


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

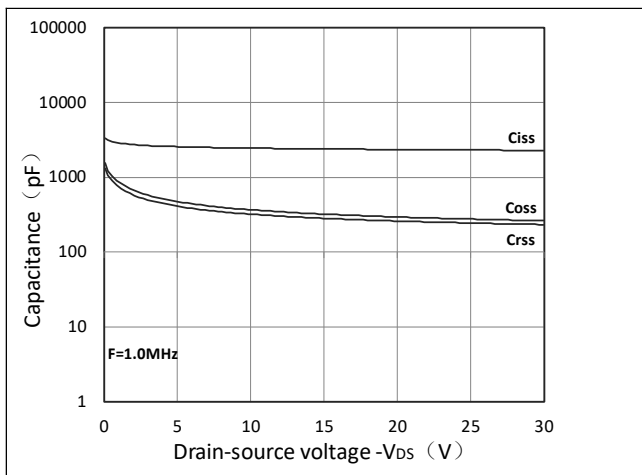


Figure 7. Capacitance Characteristics

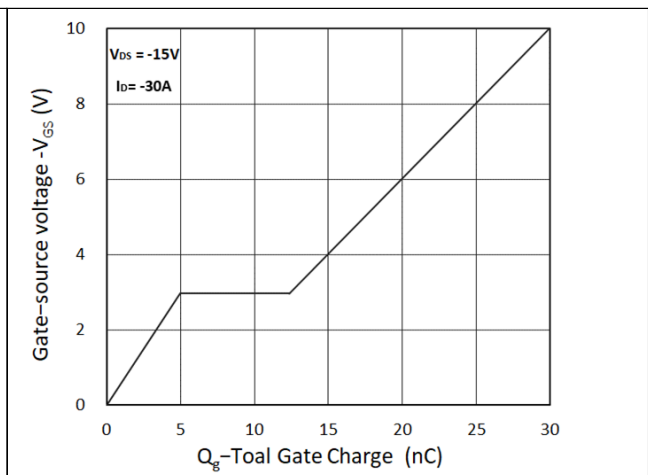


Figure 8. Gate Charge Characteristics

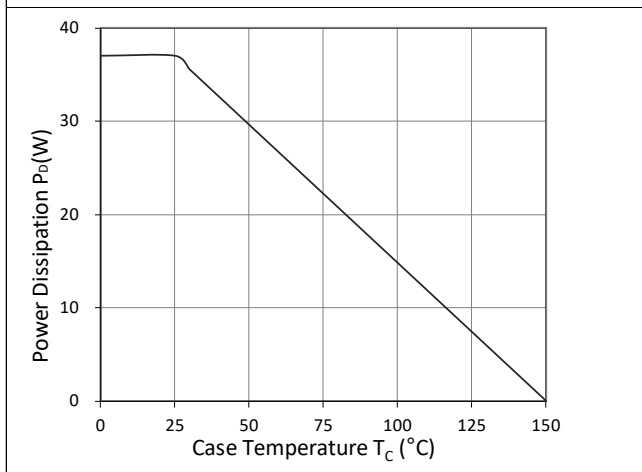


Figure 9. Power Dissipation

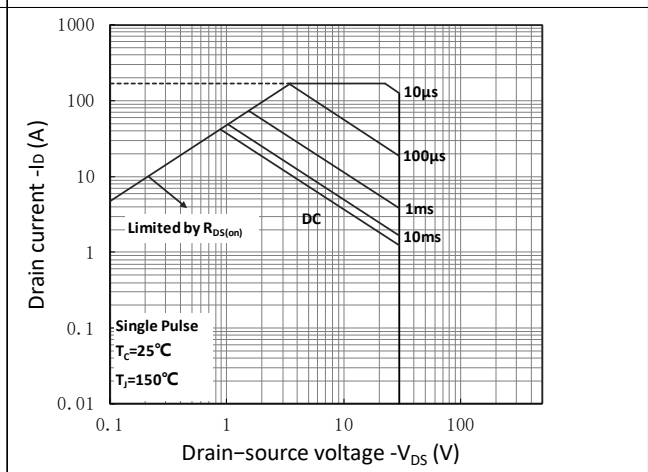


Figure 10. Safe Operating Area

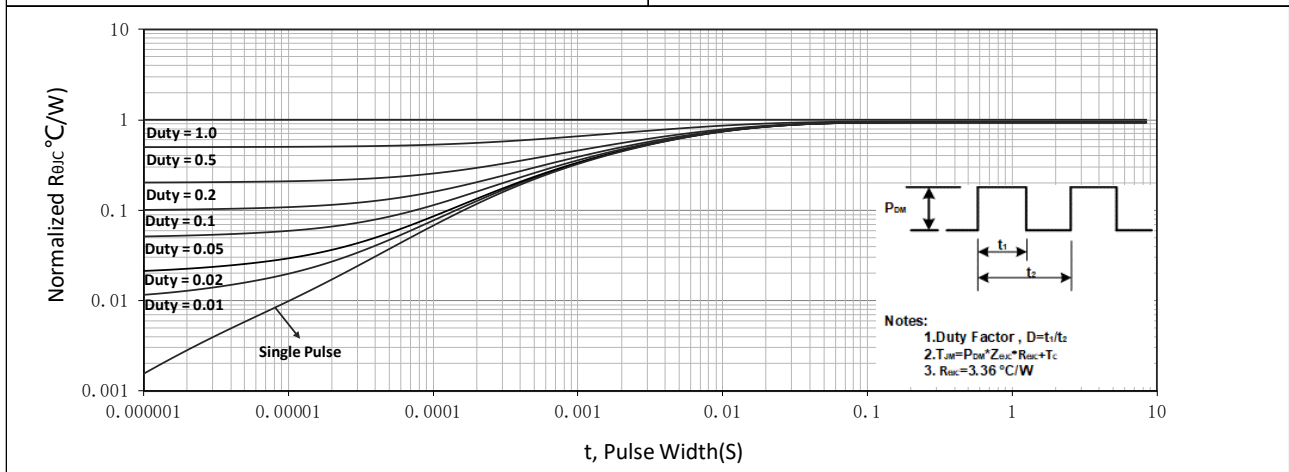
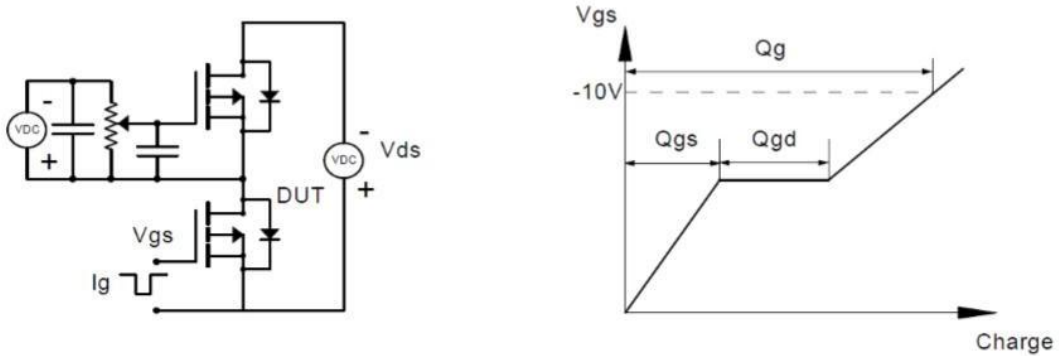


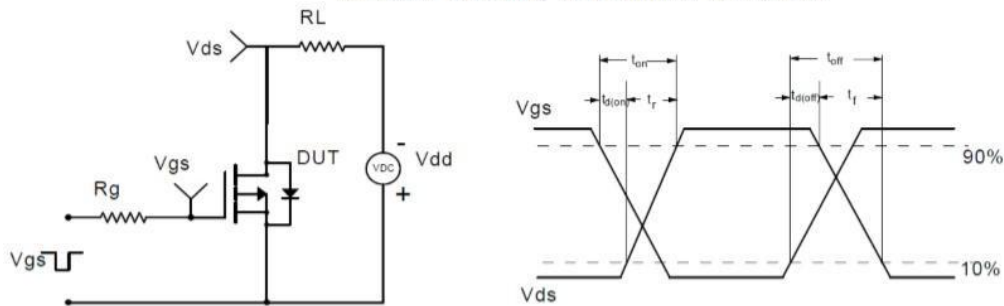
Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

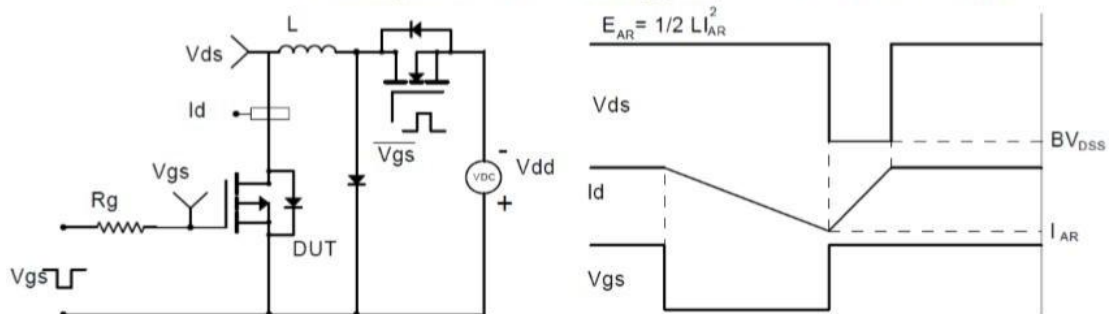
Gate Charge Test Circuit & Waveform



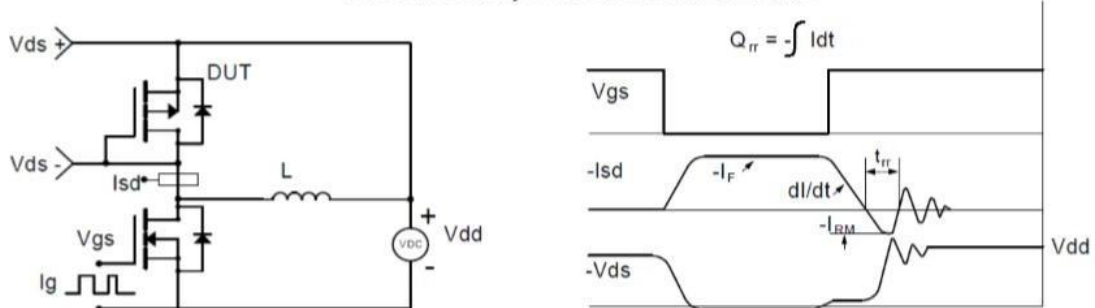
Resistive Switching Test Circuit & Waveforms



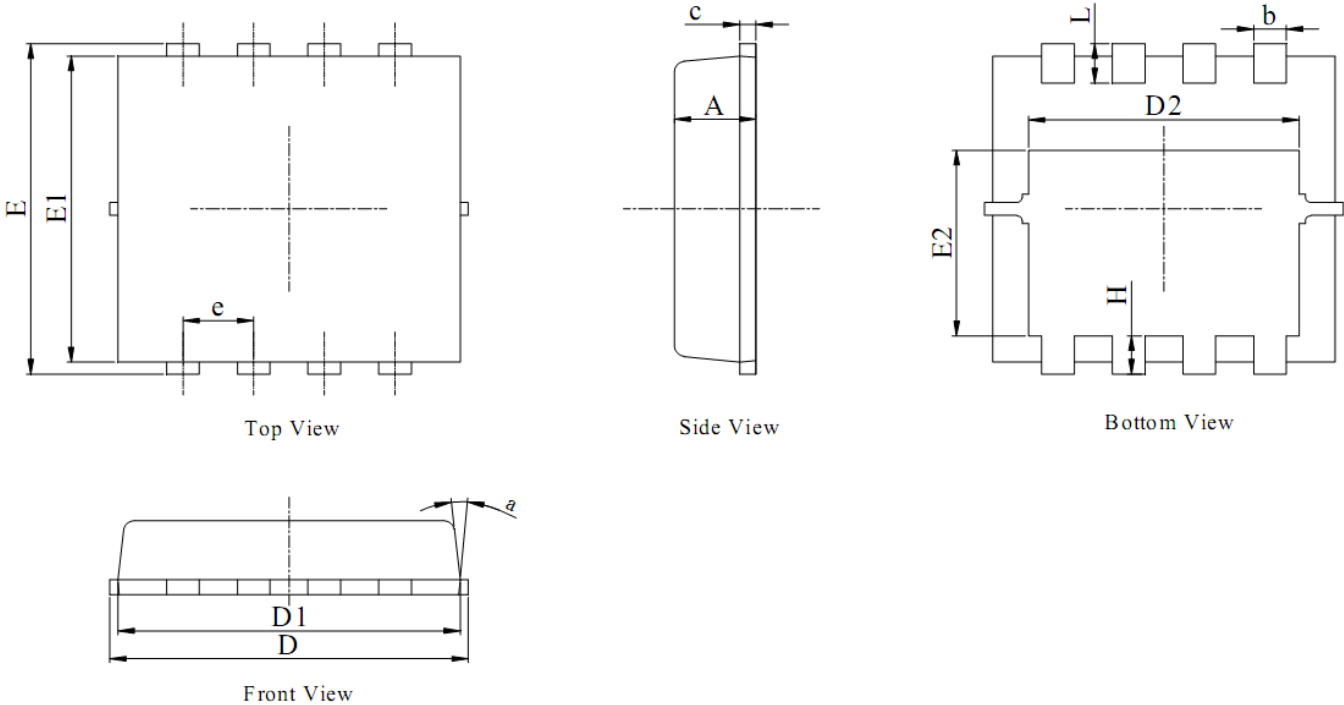
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Mechanical Data-PDFN3333-8L-Single



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMENSIONS IN MILLIMETER (ANGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°

